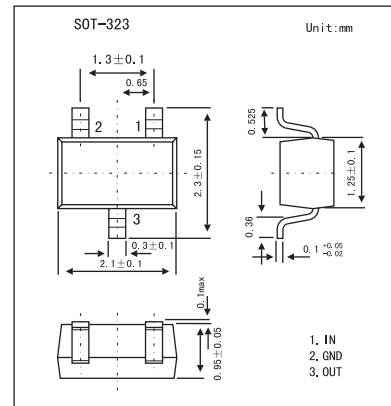


## Schottky barrier (double) diodes

1PS70SB10; 1PS70SB14  
1PS70SB15; 1PS70SB16

## ■ Features

- Low forward voltage
- Guard ring protected
- Very small plastic SMD package

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Conditions	Min	Max	Unit
Continuous reverse voltage	$V_R$			30	V
Continuous forward current	$I_F$			200	mA
Repetitive peak forward current	$I_{FRM}$	$t_p \leq 1s, \delta \leq 0.5$		300	mA
Non-repetitive peak forward current	$I_{FSM}$	$t_p < 10ms$		600	mA
Total power dissipation (per package)	$P_{tot}$	$T_{amb} < 25^\circ\text{C}$		200	mW
Storage temperature	$T_{stg}$		-65	+150	$^\circ\text{C}$
Junction temperature	$T_j$			125	$^\circ\text{C}$
Operating ambient temperature	$T_{amb}$		-65	+125	$^\circ\text{C}$
thermal resistance from junction to ambient	$R_{th(j-a)}$			625	K/W

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Conditions	Min	Max	Unit
Continuous forward voltage	$V_F$	$I_F = 0.1\text{ mA}$		240	mV
		$I_F = 1\text{ mA}$		320	mV
		$I_F = 10\text{ mA}$		400	mV
		$I_F = 30\text{ mA}$		500	mV
		$I_F = 100\text{ mA}$		800	mV
Reverse current	$I_R$	$V_R = 25\text{ V}$ , Note 1	2	15	$\mu\text{ A}$
Diode capacitance	$C_d$	$V_R = 0\text{ V}$ ; $f = 1\text{ MHz}$	10	50	pF

Note

1. Pulse test:  $t_p < 300\ \mu\text{s}$ ;  $\delta \leq 0.02$ .

## ■ Marking

Type	1PS70SB10	1PS70SB14	1PS70SB15	1PS70SB16
Marking	7*0	7*4	7*5	7*6